

AMENDMENTS

Please amend the application as indicated hereafter.

In the Claims

Please substitute the following clean copy text for the pending claims of the same number.

a¹

2. (ONCE AMENDED) The process of claim 1 wherein the step of pattern etching comprises:

- forming a patterned structure having an edge and a top; and
- forming a layer of insulator on the edge prior to the step of removing the remaining layer of silicon oxynitride.

Please add the following new claims:

a²

18. (NEW) A process comprising:

- providing a semiconductor substrate;
- forming a gate above the semiconductor substrate;
- forming a first polycrystalline silicon layer over the gate;
- forming an interpoly dielectric;
- forming a second polycrystalline silicon layer over the interpoly dielectric;
- forming a anti-reflective coating above the second polycrystalline silicon layer;

patterning the device to form a stack; and *before subjecting to T > 200°C*
removing the antireflective coating without applying an oxide between the
formation of the anti-reflective coating and the removal of the anti-reflective coating.

19. (NEW) The process of claim 18, wherein the anti-reflective coating comprises an oxide layer and a silicon oxynitride layer.

20. (NEW) The process of claim 19, wherein the silicon oxynitride is deposited by a plasma enhanced chemical vapor deposition process using the reactants N₂O and SiH₄.

21. (NEW) The process of claim 20, wherein the ratio of SiH₄ to N₂O is maintained in the range of about 0.9-1.5:1.